

The invention relates to nanoelectronics and capacitor manufacturing and can be used in optoelectronic memory systems, in photoelectric sensors, in light energy convertors, electric energy storages. A nanocomposite photo-capacitor comprises a photosensitive nanocomposite material presenting as a gallium selenide semiconductor matrix of crystalline structure. It comprises arrays of crystalline structure nanosized three-dimensional (3D) potassium nitrate ferroelectrics inclusions orderly located along hexagonal symmetry axis of layered crystalline matrix. The surface density of inclusions in the basic flat (0001) of layered crystal is more then 10^9 cm^{-2} , geometrical dimensions can not exceed single ferroelectric domain in that material. The technical result is increase of specific electric capacitance and a light overlap coefficient of solid photocapacitor within aria of low electric frequency (less than 102 Hz).